

3A 30V Low VF(1.54mm)

**Chip Information**

Chip Size	1.54 x 1.54mm
Pad Size	1.40 x 1.40mm
Chip Quantity	4616 pcs/wafer
Scribe Line Width	60um
Passivation	PSG
Wafer Size	5 inch
Top Metallization	Ti-Ag(For Solder)

Chip Thickness/Back Metal : See below "Ordering Information"

**MAXIMUM RATINGS**

Parameter	Symbol	Limit	Unit	Note
Repetitive Peak Reverse Voltage	VRRM	30	V	
Non-Repetitive Peak Reverse Voltage	VRSM		V	
Maximum DC Blocking Voltage	VR		V	
Average Forward Rectified Current	IF(AV)	3	A	
Peak Forward Surge Current	IFSM	60	A	8.3ms Single Half Sine-Wave
Storage and Operating Temperature Range	Tj,TSTG	-65 to +125	degC	

**ELECTRICAL CHARACTERISTICS**

Parameter	Symbol	Spec Limit	Probe Spec	Typical	Unit	Test Condition
Maximum Forward Voltage	VF1	0.400		0.360	V	IF=3A Ta=25degC
	VF2				V	
	VF3				V	
	VF4				V	
	VF5				V	
Maximum DC Reverse Current	IR1	3	0.8	0.36	mA	VR=30V Ta=25degC
	IR2				mA	
	IR3				mA	
	IR4				mA	
Reverse Breakdown Voltage	BV	30	35	45	V	IR=5mA
Junction Capacitance	Cj			130	pF	V=10V f=1MHz
Reverse Recovery Time	trr				nS	

**Ordering Information**

Chip Type	Chip Thickness	Back metal
YFB542	250 +/- 20um	Ti-Ni-Au (For Solder)
YFB54L	150 +/- 20um	Ti-Ni-Au (For Solder)

Note:  
Designed For